

**MOTOROLA  
SEMICONDUCTOR**  
TECHNICAL DATA

LT1839

2

$f_T = 1000$  MHz Min  
HIGH FREQUENCY  
TRANSISTOR  
NPN SILICON



CASE 79-04, STYLE 1  
(TO-39)

**The RF Line**

**NPN Silicon  
High Frequency Transistor**

. . . specifically designed for CRT driver applications requiring high frequency and high voltage, such as high resolution color graphics video monitors.

- High Voltage —  $V_{(BR)CEO} = 120$  V Min
- High Cutoff Frequency —  $f_T = 1000$  MHz Min
- Low Output Capacitance —  $C_{cb} = 2.5$  pF Max @  $V_{CB} = 15$  V
- Gold Metallization

**MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	$V_{CEO}$	70	Vdc
Collector-Base Voltage	$V_{CBO}$	120	Vdc
Emitter-Base Voltage	$V_{EBO}$	3	Vdc
Collector Current — Continuous	$I_C$	300	mAdc
Operating Junction Temperature	$T_J$	200	°C
Storage Temperature Range	$T_{stg}$	-65 to +200	°C

**ELECTRICAL CHARACTERISTICS**

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector-Emitter Breakdown Voltage ( $I_C = 1$ mA, $I_B = 0$ )	$V_{(BR)CEO}$	70	—	—	Vdc
Collector-Base Breakdown Voltage ( $I_C = 0.1$ mA, $I_E = 0$ )	$V_{(BR)CBO}$	120	—	—	Vdc
Emitter-Base Breakdown Voltage ( $I_E = 0.1$ mA, $I_C = 0$ )	$V_{(BR)EBO}$	3	—	—	Vdc
Collector Cutoff Current ( $V_{CB} = 80$ V, $I_E = 0$ )	$I_{CBO}$	—	—	20	μAdc
Collector Cutoff Current ( $V_{CE} = 80$ V, $V_{BE} = 0$ )	$I_{CES}$	—	—	100	μAdc
<b>ON CHARACTERISTICS</b>					
DC Current Gain ( $I_C = 50$ mA, $V_{CE} = 5$ V)	$h_{FE}$	20	—	60	—
Collector-Emitter Saturation Voltage ( $I_C = 50$ mA, $I_B = 5$ mA)	$V_{CE(sat)}$	—	—	800	mV
<b>DYNAMIC CHARACTERISTICS</b>					
Collector-Base Capacitance ( $V_{CB} = 15$ V, $I_E = 0$ , $f = 1$ MHz)	$C_{cb}$	—	—	2.5	pF

**FUNCTIONAL TESTS**

Cutoff Frequency ( $V_{CE} = 10$ V, $I_C = 80$ mA, $f = 250$ MHz)	$f_T$	1	—	—	GHz
Insertion Gain ( $V_{CE} = 10$ V, $I_C = 50$ mA, $f = 200$ MHz)	$ S_{21} ^2$	13	—	—	dB

## TYPICAL CHARACTERISTICS

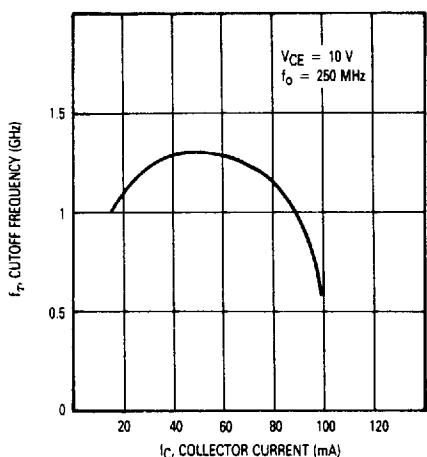


Figure 1. Gain Bandwidth Product versus Collector Current

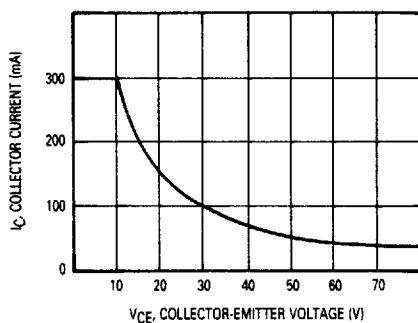


Figure 2. Safe Operating Area

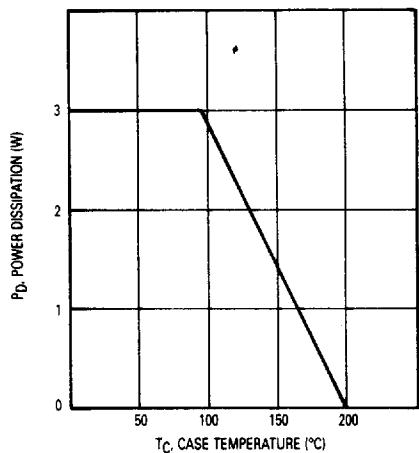


Figure 3. Power Dissipation versus Temperature

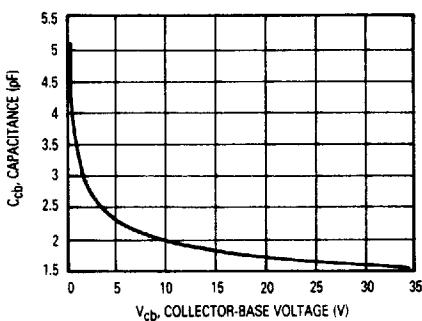


Figure 4. Junction Capacitance versus Voltage